



**Advanced N-Ch Power MOSFET** 

### SWITCHING REGULATOR APPLICATIONS

### **Features**

• High Voltage: BV<sub>DSS</sub>=500V(Min.)

• Low Crss: Crss=23pF(Typ.)

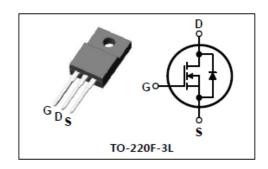
• Low gate charge : Qg=30nC(Typ.) • Low RDS(on) : RDS(on)=0.8 $\Omega$ (Max.)

## **Ordering Information**

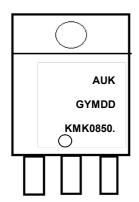
Type NO.	Marking	Package Code

KMK0850F KMK0850• TO-220F-3L

#### **PIN** Connection



## **Marking Diagram**



Da Lian

Column 1 : Manufacturer

Column 2: Production Information

e.g.) GYMDD

-. G: Factory management code

-. YMDD: Date Code (year, month, date)

Column 3: Device Code

## Absolute maximum ratings (Tc=25 C unless otherwise noted)

Characteristic	Symbol		Rating	Unit		
Drain-source voltage		V <sub>DSS</sub>	500	V		
Gate-source voltage	V <sub>GSS</sub>		±30	V		
Drain current (DC) *	ΙD	Tc=25℃	8	А		
	10	Tc=100°C	4.5	Α		
Drain current (Pulsed)*	Ідм		32	Α		
Power dissipation	PD		40	W		
Avalanche current (Single) ②	Ias		8	Α		
Single pulsed avalanche energy ②	Eas		Eas		360	mJ
Avalanche current (Repetitive) ①	Iar		8	A		
Repetitive avalanche energy ①	Ear		7.5	mJ		
Junction temperature T <sub>J</sub>		Tı	150	°C		
Storage temperature range	$T_{stg}$		-55~150			

<sup>\*</sup> Limited by maximum junction temperature

Characteristic		Symbol	Тур.	Max	Unit
Thermal	Junction-case	Rth(J-C)	-	3.12	°C/W
resistance	Junction-ambient	Rth(J-A)	-	62.5	°C/W

## Electrical Characteristics (Tc=25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit	
Drain-source breakdown voltage	BV <sub>DSS</sub>	In=250uA, Vgs=0V	500	-	-	V	
Gate threshold voltage	V <sub>GS(th)</sub>	In=250uA, Vns=Vgs	2.0	-	4.0	V	
		V <sub>DS</sub> =500V, V <sub>GS</sub> =0V	-	-	1		
Drain-source cut-off current	IDSS	V <sub>DS</sub> =500V, V <sub>GS</sub> =0V T <sub>C</sub> =125°C	-	-	200	uA	
Gate leakage current	Igss	$V_{DS}=0V$ , $V_{GS}=\pm30V$	-	-	±100	nA	
Drain-source on-resistance 4	RDS(on)	V <sub>G</sub> S=10V, I <sub>D</sub> =4.0A	-	0.68	0.80	Ω	
Forward transfer conductance ④	<b>G</b> fs	V <sub>DS</sub> =10V, I <sub>D</sub> =4.0A	-	6.5	-	S	
Input capacitance	Ciss		-	1216	1520		
Output capacitance	Coss	VGS=0V, VDS=25V f=1 MHz	-	119	149	pF	
Reverse transfer capacitance	Crss		-	23	29		
Turn-on delay time	td(on)		-	18	-		
Rise time	tr	VDD=250V, ID=8A	-	65	-		
Turn-off delay time	td(off)	$R_G=25\Omega$ 34	-	93	-	ne	
Fall time	tf		-	64	-	ns	
Total gate charge	Qg	V 200 V 10V	-	26	32		
Gate-source charge	Qgs	V <sub>DS</sub> =200,V <sub>GS</sub> =10V I <sub>D</sub> =8A 34	-	7.7	-	nC	
Gate-drain charge	Qgd		-	6.4	-		

# Source-Drain Diode Ratings and Characteristics (Tc=25°C unless otherwise noted)

			,			
Characteristic	Symbol	<b>Test Condition</b>	Min.	Typ.	Max.	Unit
Source current (DC)	Is	Integral reverse diode	-	-	8	۸
Source current (Pulsed) ①	Ism	in the MOSFET	-	-	32	Α
Forward voltage 4	VsD	V <sub>G</sub> s=0V, I <sub>S</sub> =8A	-	-	1.4	V
Reverse recovery time	trr	Is=8A, V <sub>G</sub> s=0V	-	335	-	ns
Reverse recovery charge	Qrr	dI <sub>F</sub> /dt=100A/us	-	2.95	-	uC

### Note;

① Repetitive rating: Pulse width limited by maximum junction temperature

② L=10.2 mH, IAS=8A, VDD=50V, RG=25 $\Omega$ , Starting TJ=25 $^{\circ}$ C

③ Pulse Test: Pulse width≤300us, Duty cycle≤2%

4 Essentially independent of operating temperature

### **Electrical Characteristic Curves**

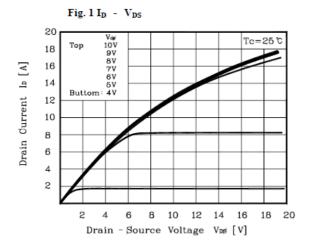


Fig. 2 I<sub>D</sub> - V<sub>GS</sub>

Note:
1. V<sub>DS</sub>=10V
2. Pulse test

150°C

150°C

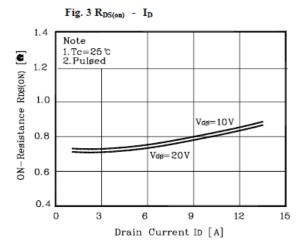
25°C

25°C

25°C

25°C

30 Gate-Source Voltage Vds [V]



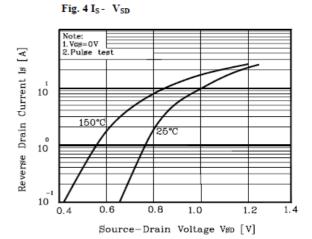
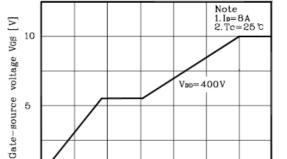


Fig.6 V<sub>GS</sub> - Q<sub>G</sub>

5 10

0





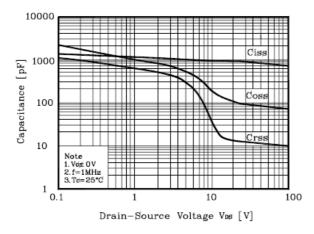
15

20

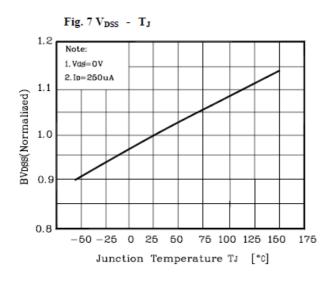
Total Gate Charge Qc [nC]

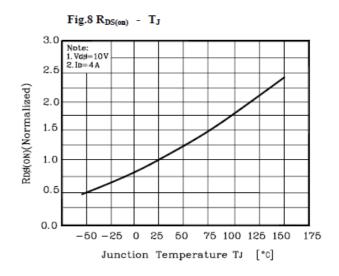
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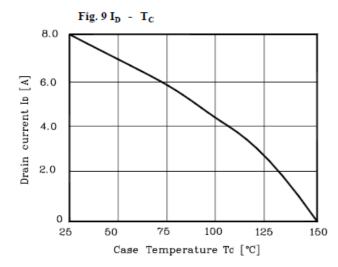
35



## **Electrical Characteristic Curves**







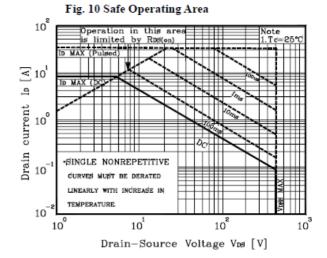


Fig. 11 Gate Charge Test Circuit & Waveform

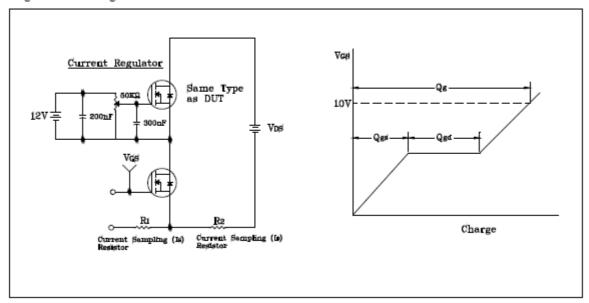


Fig. 12 Resistive Switching Test Circuit & Waveform

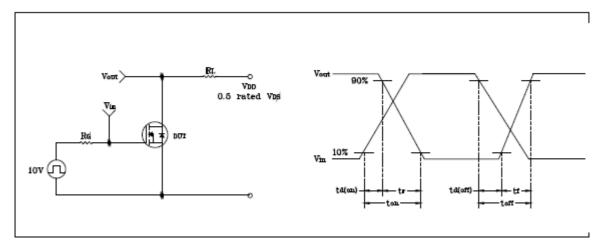


Fig. 13 E<sub>AS</sub> Test Circuit & Waveform

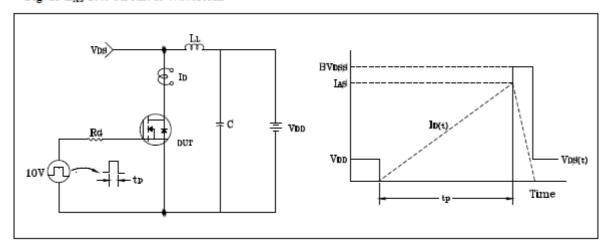
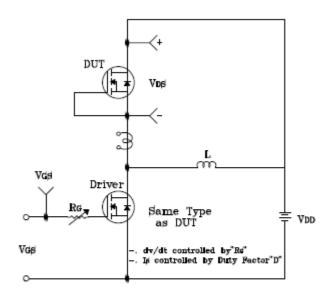
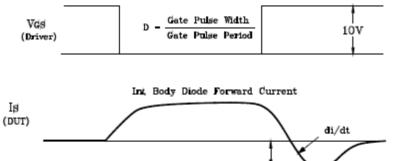
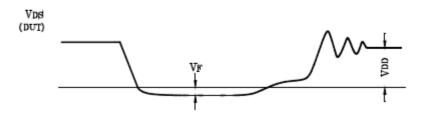


Fig. 14 Diode Reverse Recovery Time Test Circuit & Waveform



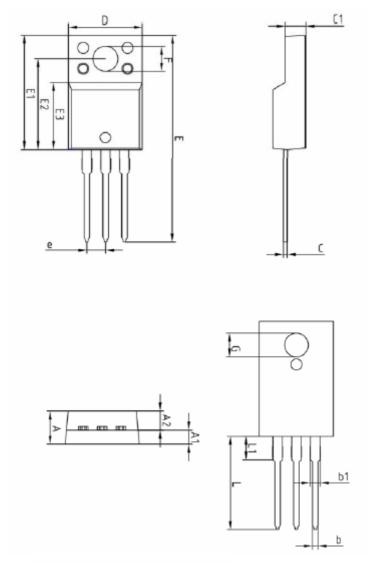




AUK Dalian 6

Body Diode Reverse Current

Outline Dimension unit: mm



		MILLIMETER		_
SYMBOL		NOTE		
31neor.	MINIMUM	NOMINAL	MAXIMUM	HOTE
A	_	_	4.60	
A1	2.45	2.50	2.55	
A2	1.95	2.00	2.05	
ь	0.65	0.75	0.85	
ь1	1.07	1.27	1.47	
С	0.40	0.50	0.60	
C1	2.70	2.80	2.90	
D	9.90	10.00	10.10	
E	28.00	-	28.60	
E1	15.50	15.60	15.70	
E2	12.30	12.40	12.50	
E3	9.15	9.20	9.25	
F	3.30	3.40	3.50	
G	3.10	3.20	3.30	
е				
L	12.40	_	13.00	
L1				

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